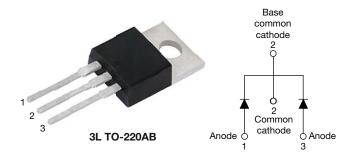
HALOGEN



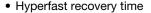
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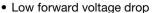
# Hyperfast Rectifier, 2 x 15 A FRED Pt®



PRIMARY CHARACTERISTICS								
Package	3L TO-220AB							
$I_{F(AV)}$	2 x 15 A							
V <sub>R</sub>	300 V							
V <sub>F</sub> at I <sub>F</sub>	0.85 V							
t <sub>rr</sub> typ.	See Recovery table							
T <sub>J</sub> max.	175 °C							
Circuit configuration	Common cathode							

#### **FEATURES**





175 °C operating junction temperature

Low leakage current

**FREE** Designed and qualified according to JEDEC®-JESD 47

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	$V_{RRM}$		300	V					
Average rectified forward current	per diode	I <sub>F(AV)</sub>	T <sub>C</sub> = 153 °C	15					
	per device			30	Α				
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	150					
Operating junction and storage tem	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C					

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	300	-	-	.,			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	1.0	1.25	V			
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	0.85	0.95				
Davaga laakaga august		$V_R = V_R$ rated	-	-	40				
Reverse leakage current	I <sub>R</sub>	$T_J = 125 ^{\circ}\text{C},  V_R = V_R  \text{rated}$ - 8		8	200	μΑ			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 300 V	-	38	-	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH			



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 A, dI_F/dt = 50$	$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	36			
	t <sub>rr</sub>	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	30			
		T <sub>J</sub> = 25 °C		-	33	-	ns A		
		T <sub>J</sub> = 125 °C		-	48	-			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	l <sub>F</sub> = 15 A dl <sub>F</sub> /dt = 200 A/μs	-	2.8	-			
		T <sub>J</sub> = 125 °C	$V_{\rm R} = 200 \text{ V}$	-	6.5	-			
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	46	-			
	$Q_{rr}$	T <sub>J</sub> = 125 °C		-	160	-			

THERMAL MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>	-65	-	175	°C				
Thermal resistance, junction to case per diode	$R_{thJC}$	-	-	1.4	°C/W				
Marking device		Case style 3L TO-220AB 30CTH03							

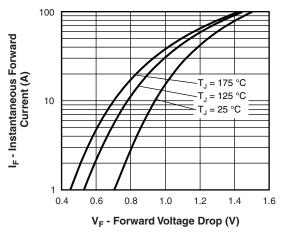


Fig. 1 - Typical Forward Voltage Drop Characteristics

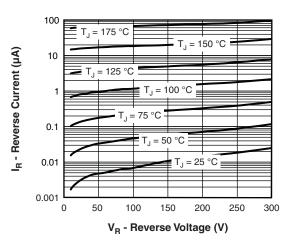


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

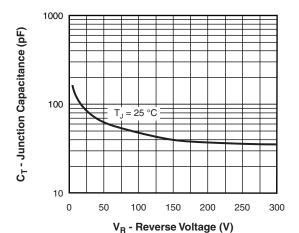


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

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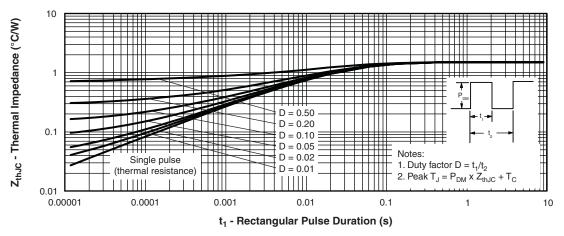


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

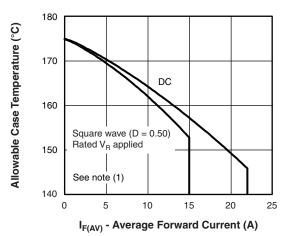


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

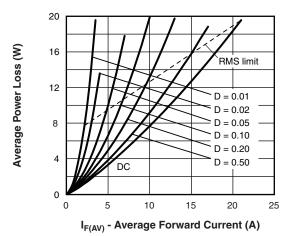


Fig. 6 - Forward Power Loss Characteristics

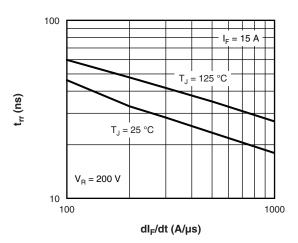


Fig. 7 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

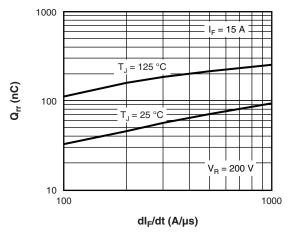
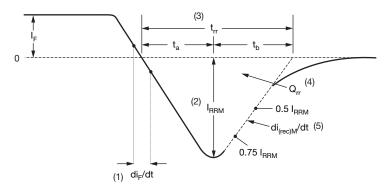


Fig. 8 - Typical Stored Charge vs.  $dI_F/dt$ 

#### Note

(1) Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>thJC</sub>; Pd = forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>

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- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

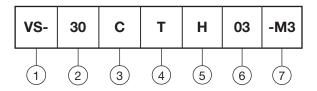
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- Current rating (30 = 30 A)
- 3 Circuit configuration:

C = common cathode

4 - Package:

T = 3L TO-220AB

5 - H = hyperfast recovery

6 - Voltage rating (03 = 300 V)

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-30CTH03-M3	50	1000	Antistatic plastic tube						

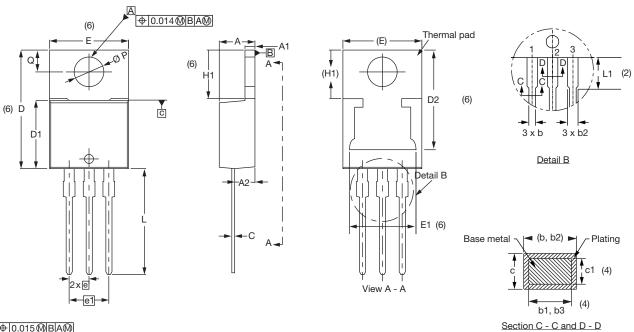
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96154						
Part marking information	www.vishay.com/doc?95028						



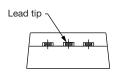
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### **3L TO-220AB**

### **DIMENSIONS** in millimeters and inches



**⊕** 0.015 **M** B A **M** 



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183		D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055		E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115		E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040		е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4	e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068		H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4	L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024		L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4	ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3	Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355							

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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